

5DS04B

Switching Diode



Features

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- High – speed

Item	Characteristics
Wafer size	5inch
Chip size	260*260um

Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V _{RSM}	100	V
Repetitive Peak Reverse Voltage	V _{RRM}	75	V
Repetitive Peak Forward Current	I _{FRM}	500	mA
Continuous Forward Current	I _O	150	mA
Non-Repetitive Peak Forward Current @t=1us	I _{FSM}	2	A
Power Dissipation	PD	500	mW
Junction Temperature	T _j	175	degC
Storage Temperature	T _{stg}	-65to+175	degC

Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	V _F		0.98	V	I _F =100mA
Breakdown Voltage	V _B	100		V	I _R =100uA
Reverse Current	I _R		25	nA	V _R =20V
Junction Capacitance	C _T		4	pF	V _R =0V, f=1MHz
Reverse Recovery Time	t _{rr}		4	nsec	I _F =10mA, V _R =6V, R _L =100Ω, irr=1mA

Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
V _F		0.98	V	I _F =100mA
V _B	105		V	I _R =100uA
I _{R1}		25	nA	V _R =30V
I _{R2}		2	uA	V _R =85V
C _T		4	pF	V _R =0V, f=1MHz
t _{rr}		4	nsec	I _F =10mA, V _R =6V, R _L =100Ω, irr=1mA

Note Equivalent type : 1N4448

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